/ Revised record

F	2018-4				
G	2018-10-22				
H	2019-1-09	1			
I	2019-6-13		取消 RDSON@-20V/-10A 的项目		
J	2022-1-10		VGSS=±20V ±25V; IGSS VGSS=±20V ±25V E		
A	2022-2-25	ALL	AOS-AOSP21307 BRCS4407SC		

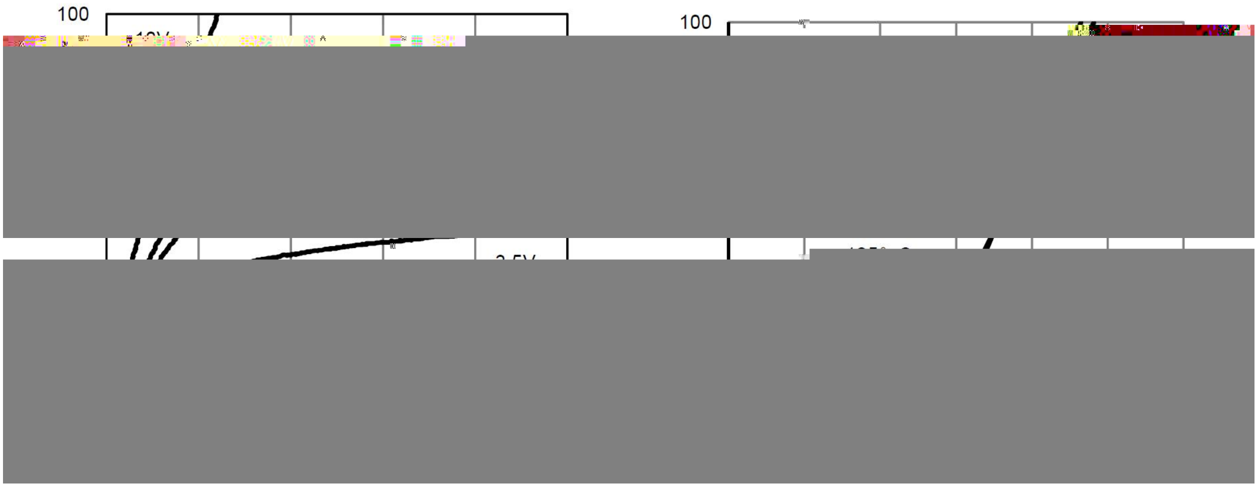
SOP-8 P MOS
P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

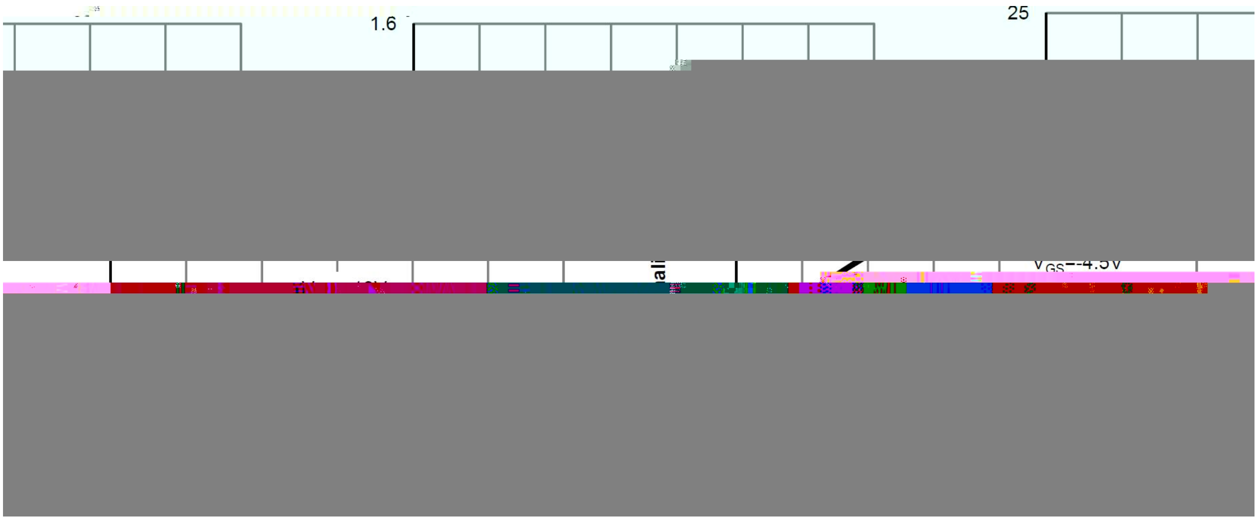
V_{DS} (V) = -30V
I_D = -14A (V_{GS} = ± 25v ǂ Ң b

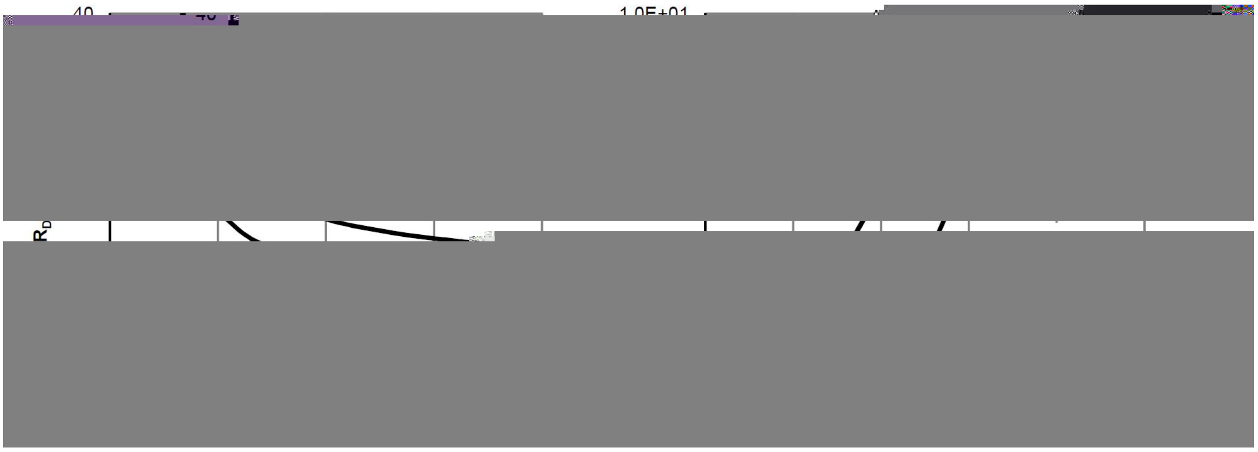
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	±25	V
Continuous Drain Current	I_D (T_a=25°C)	-14	A
Pulsed Drain Current	I_{DM}	-56	A
Power Dissipation for Single Operation	P_D (T_a=25℃)	3.1	W
Maximum Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

* Thermal Resistance- 9

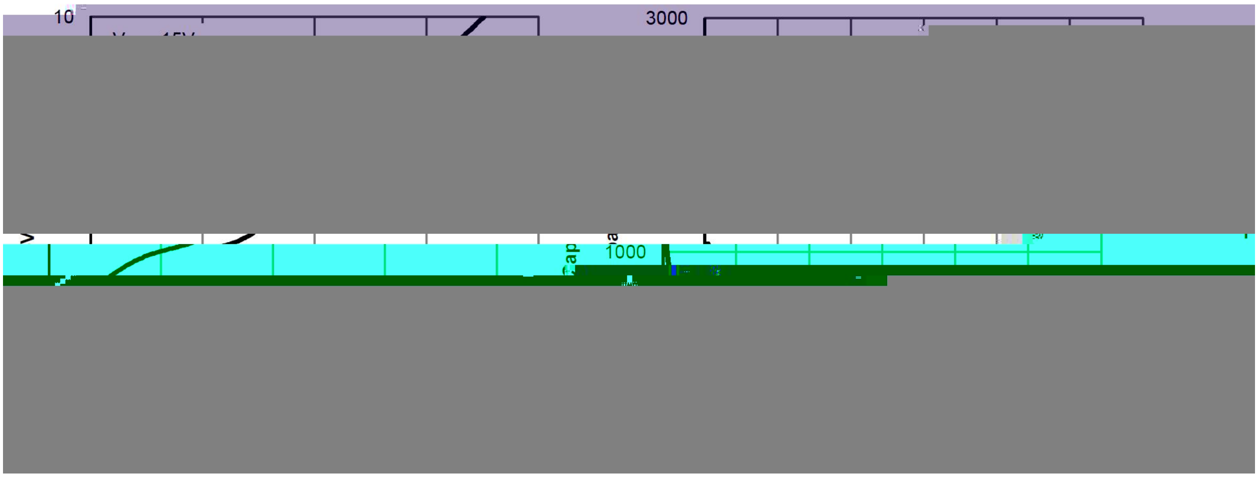
/ Electrical Characteristic Curve

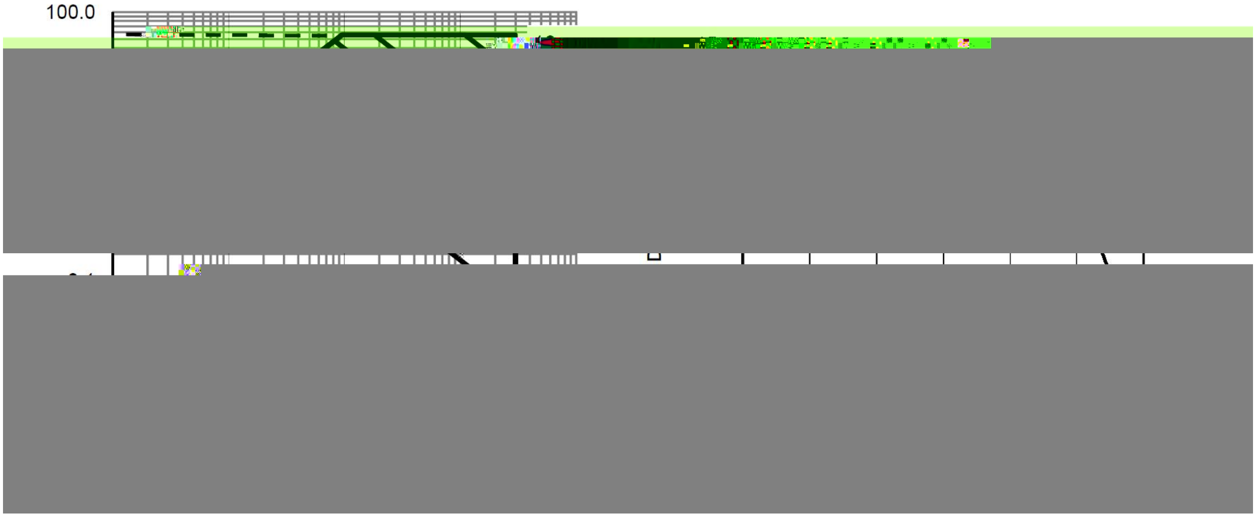


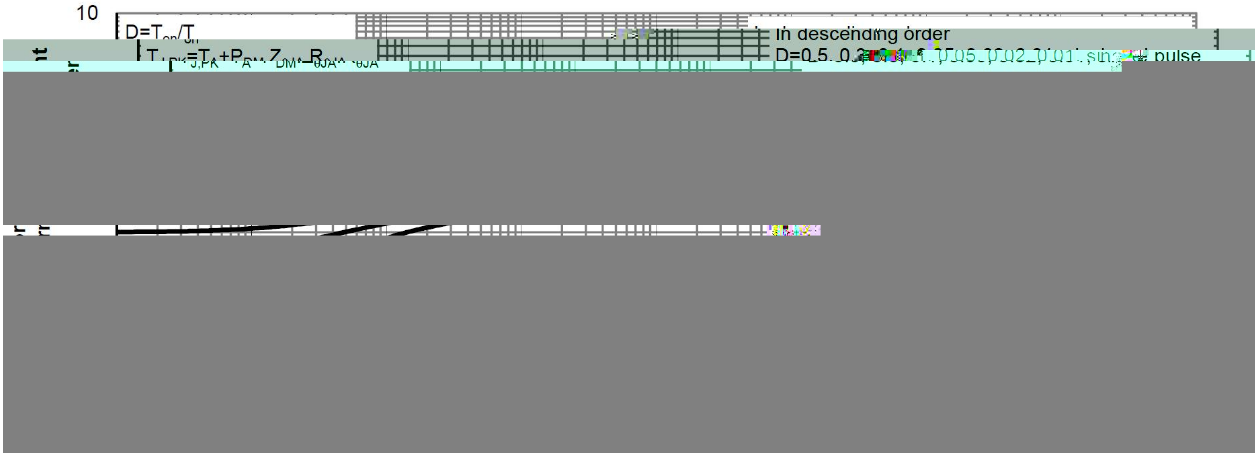




/ Electrical Characteristic Curve



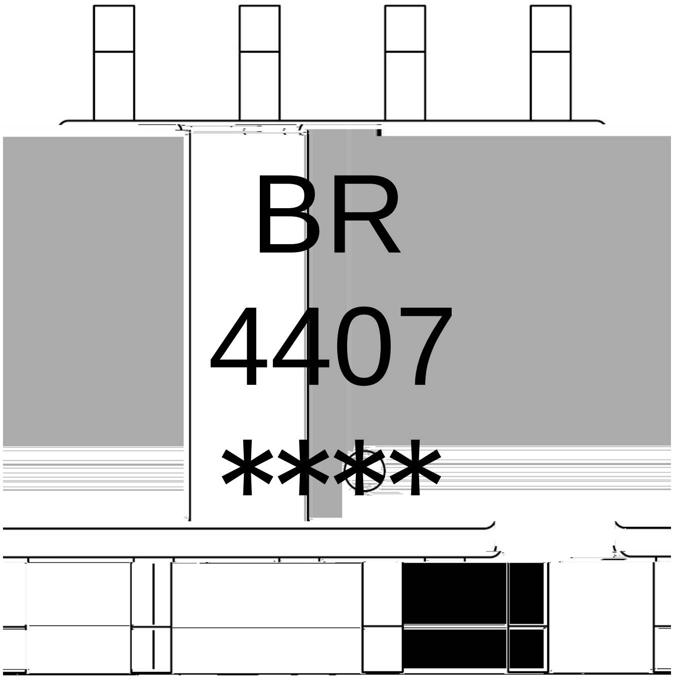




/ Package Dimensions

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
[illegible]	4.70	5.10	[illegible]	1.25	1.75
B	3.70	4.10	[illegible]	0.35	0.49

/ Marking Instructions



BR

4407

****

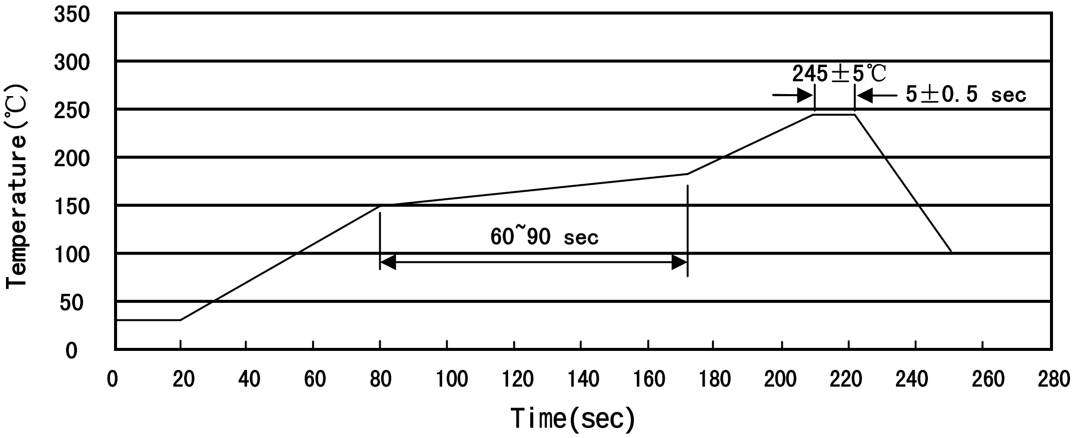
Note:

BR: Company Code

4407: Product Type

****: Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



	Note:
1 150 180 60 90sec;	1.Preheating:150~180℃, Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3 2 10℃/sec.	3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃ 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
							盒	箱
						〃		

/ Notices